

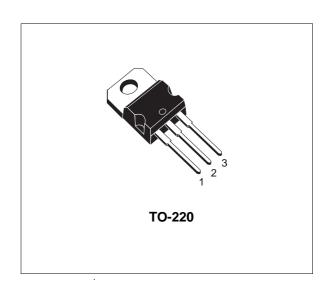
TIP120/121/122 TIP125/126/127

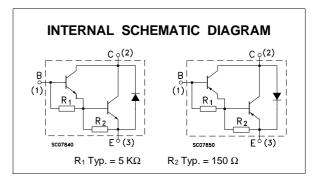
COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

 STMicroelectronics PREFERRED SALESTYPES

DESCRIPTION

The TIP120, TIP121 and TIP122 are silicon Epitaxial-Base NPN power transistors in monolithic Darlington configuration mounted in Jedec TO-220 plastic package. They are intented for use in power linear and switching applications. The complementary PNP types are TIP125, TIP126 and TIP127, respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	ol Parameter			Value			
		NPN	TIP120	TIP121	TIP122		
		PNP	TIP125	TIP126	TIP127		
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	80	100	V	
V_{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V	
V _{EBO}	Emitter-Base Voltage (I _C = 0)			5		V	
Ic	Collector Current			5		Α	
I _{CM}	Collector Peak Current			8		Α	
Ι _Β	Base Current			0.1		Α	
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C			65		W	
	T _{amb} ≤ 25 °C			2		W	
T_{stg}	Storage Temperature			-65 to 150		°C	
Tj	Max. Operating Junction Temperature		150			°C	

^{*} For PNP types voltage and current values are negative.

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TIP120/TIP121/TIP122/TIP125/TIP126/TIP127

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.92	°C/W	
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W	

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

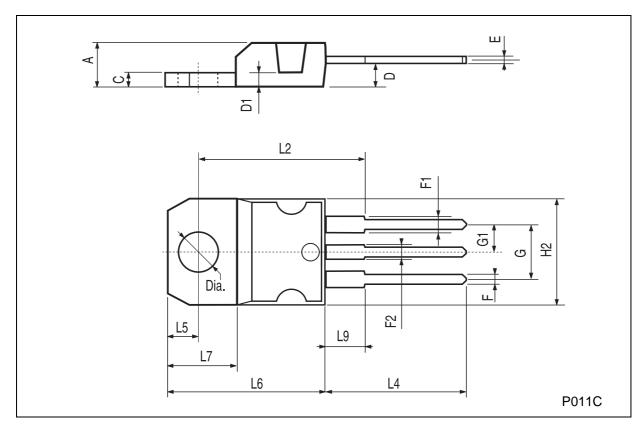
Symbol	Parameter	Test Co	nditions	Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP120/125 for TIP121/126 for TIP122/127	$V_{CE} = 30 V$ $V_{CE} = 40 V$ $V_{CE} = 50 V$			0.5 0.5 0.5	mA mA mA
Ісво	Collector Cut-off Current (I _B = 0)	for TIP120/125 for TIP121/126 for TIP122/127	V _{CB} = 60 V V _{CB} = 80 V V _{CB} = 100 V			0.2 0.2 0.2	mA mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				2	mA
VCEO(sus)*	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP120/125 for TIP121/126 for TIP122/127		60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 3 A I _C = 5 A	I _B = 12 mA I _B = 20 mA			2 4	V V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 3 A	V _{CE} = 3 V			2.5	V
h _{FE} *	DC Current Gain	I _C = 0.5 A I _C = 3 A	V _{CE} = 3 V V _{CE} = 3 V	1000 1000			

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^{*} Pulsed: Pulse duration = 300 μs, duty cycle < 2 % For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
E	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



TIP120/TIP121/TIP122/TIP125/TIP126/TIP127

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